

March 1997

4A, 400V - 600V Ultrafast Diodes

Features

- Ultrafast with Soft Recovery <55ns
- Operating Temperature +175°C
- Reverse Voltage Up To 600V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Description

RURD440, RURD450, RURD460, RURD440S, RURD450S and RURD460S (TA49035) are ultrafast diodes with soft recovery characteristics ($t_{RR} < 55ns$). They have low forward voltage drop and are silicon nitride passivated ion-implanted epitaxial planar construction.

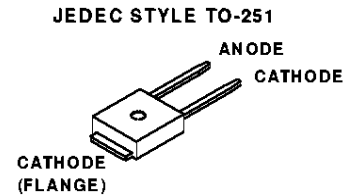
These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

PACKAGING AVAILABILITY

| PART NUMBER | PACKAGE | BRAND |
|-------------|---------|--------|
| RURD440 | TO-251 | RUR440 |
| RURD450 | TO-251 | RUR450 |
| RURD460 | TO-251 | RUR460 |
| RURD440S | TO-252 | RUR440 |
| RURD450S | TO-252 | RUR450 |
| RURD460S | TO-252 | RUR460 |

NOTE: When ordering, use the entire part number.

Package



Symbol



Absolute Maximum Ratings $T_C = +25^\circ C$, Unless Otherwise Specified

| | RURD440 RURD440S | RURD450 RURD450S | RURD460 RURD460S | UNITS |
|---|---------------------|---------------------|---------------------|-------|
| Peak Repetitive Reverse Voltage V_{RRM} | 400 | 500 | 600 | V |
| Working Peak Reverse Voltage V_{RWM} | 400 | 500 | 600 | V |
| DC Blocking Voltage V_R | 400 | 500 | 600 | V |
| Average Rectified Forward Current $I_{F(AV)}$ ($T_C = +160^\circ C$) | 4 | 4 | 4 | A |
| Repetitive Peak Surge Current I_{FSM} (Square Wave, 20kHz) | 8 | 8 | 8 | A |
| Nonrepetitive Peak Surge Current I_{FSM} (Halfwave, 1 phase, 60Hz) | 40 | 40 | 40 | A |
| Maximum Power Dissipation P_D | 50 | 50 | 50 | W |
| Avalanche Energy ($L = 40mH$) E_{AVL} | 10 | 10 | 10 | mj |
| Operating and Storage Temperature T_{STG}, T_J | -65 to +175 | -65 to +175 | -65 to +175 | °C |

Specifications RURD440, RURD450, RURD460, RURD440S, RURD450S, RURD460S

Electrical Specifications $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

| SYMBOL | TEST CONDITION | LIMITS | | | | | | | | | UNITS |
|-----------------|--|-------------------|-----|-----|-------------------|-----|-----|-------------------|-----|-----|---------------------------|
| | | RURD440, RURD440S | | | RURD450, RURD450S | | | RURD460, RURD460S | | | |
| | | MIN | TYP | MAX | MIN | TYP | MAX | MIN | TYP | MAX | |
| V_F | $I_F = 4\text{A}, T_C = +25^\circ\text{C}$ | - | - | 1.5 | - | - | 1.5 | - | - | 1.5 | V |
| V_F | $I_F = 4\text{A}, T_C = +150^\circ\text{C}$ | - | - | 1.2 | - | - | 1.2 | - | - | 1.2 | V |
| I_R | $V_R = 400\text{V}, T_C = +25^\circ\text{C}$ | - | - | 100 | - | - | - | - | - | - | μA |
| | $V_R = 500\text{V}, T_C = +25^\circ\text{C}$ | - | - | - | - | - | 100 | - | - | - | μA |
| | $V_R = 600\text{V}, T_C = +25^\circ\text{C}$ | - | - | - | - | - | - | - | - | 100 | μA |
| I_R | $V_R = 400\text{V}, T_C = +150^\circ\text{C}$ | - | - | 500 | - | - | - | - | - | - | μA |
| | $V_R = 500\text{V}, T_C = +150^\circ\text{C}$ | - | - | - | - | - | 500 | - | - | - | μA |
| | $V_R = 600\text{V}, T_C = +150^\circ\text{C}$ | - | - | - | - | - | - | - | - | 500 | μA |
| t_{RR} | $I_F = 1\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | - | - | 55 | - | - | 55 | - | - | 55 | ns |
| | $I_F = 4\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | - | - | 60 | - | - | 60 | - | - | 60 | ns |
| t_A | $I_F = 4\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | - | 32 | - | - | 32 | - | - | 32 | - | ns |
| t_B | $I_F = 4\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | - | 15 | - | - | 15 | - | - | 15 | - | ns |
| Q_{RR} | $I_F = 4\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | - | 50 | - | - | 50 | - | - | 50 | - | nC |
| C_J | $V_R = 10\text{V}, I_F = 0\text{A}$ | - | 15 | - | - | 15 | - | - | 15 | - | pF |
| $R_{\theta JC}$ | | - | - | 3 | - | - | 3 | - | - | 3 | $^\circ\text{C}/\text{W}$ |

DEFINITIONS

V_F = Instantaneous forward voltage ($p_w = 300\mu\text{s}$, $D = 2\%$).

I_R = Instantaneous reverse current.

t_{RR} = Reverse recovery time (See Figure 2), summation of $t_A + t_B$.

t_A = Time to reach peak reverse current (See Figure 2).

t_B = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 2).

$R_{\theta JC}$ = Thermal resistance junction to case.

E_{AVL} = Controlled avalanche energy (See Figures 9 and 10).

p_w = pulse width.

D = duty cycle.

V_1 AMPLITUDE CONTROLS I_F
 V_2 AMPLITUDE CONTROLS di_F/dt
 L_1 = SELF INDUCTANCE OF
 $R_4 + L_{LOOP}$

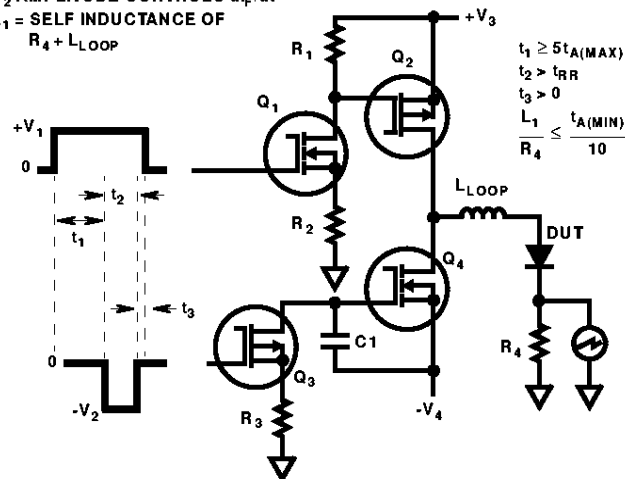


FIGURE 1. t_{RR} TEST CIRCUIT

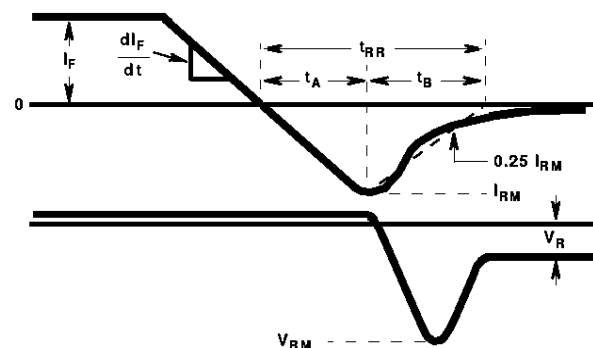


FIGURE 2. t_{RR} WAVEFORMS AND DEFINITIONS

Typical Performance Curves

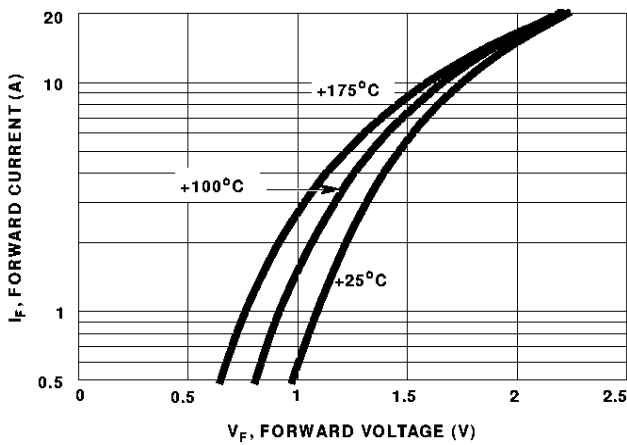


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

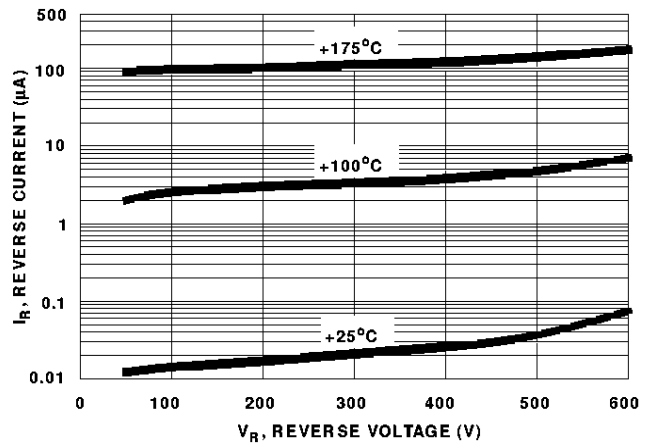


FIGURE 4. TYPICAL REVERSE CURRENT vs REVERSE VOLTAGE

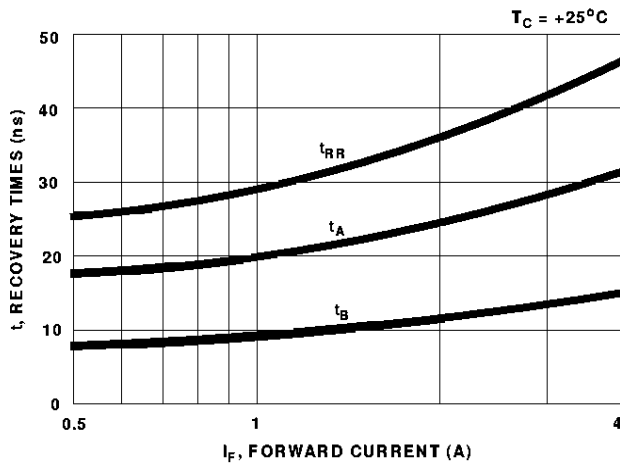


FIGURE 5. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT

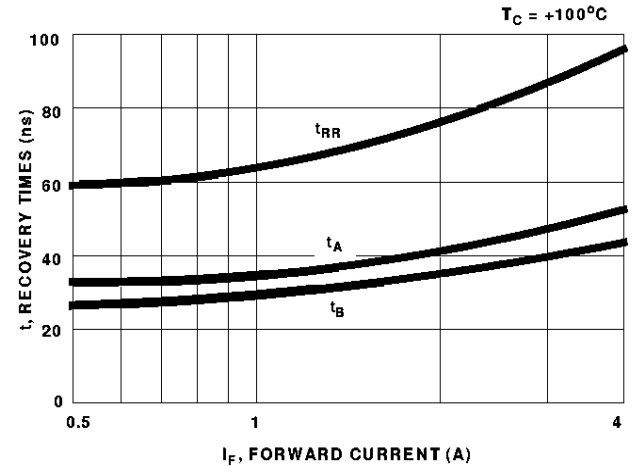


FIGURE 6. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT

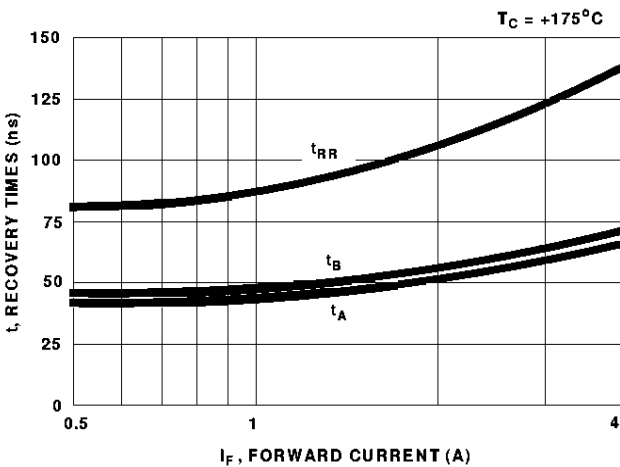


FIGURE 7. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT

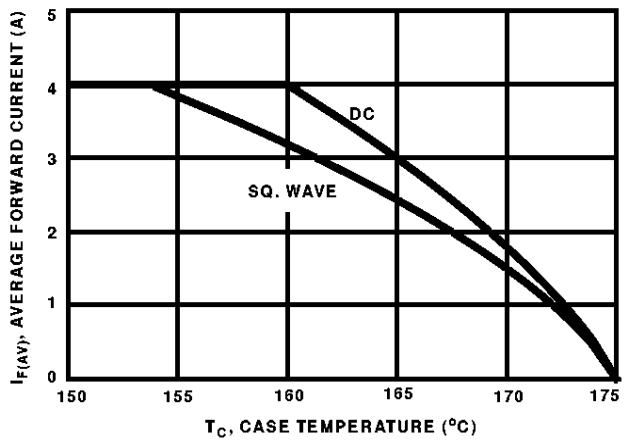


FIGURE 8. CURRENT DERATING CURVE FOR ALL TYPES

$I_{MAX} = 1A$

$L = 40mH$

$R < 0.1\Omega$

$E_{AVL} = 1/2LI^2 [V_{AVL} / (V_{AVL} - V_{DD})]$

Q_1 AND Q_2 ARE 1000V MOSFETs

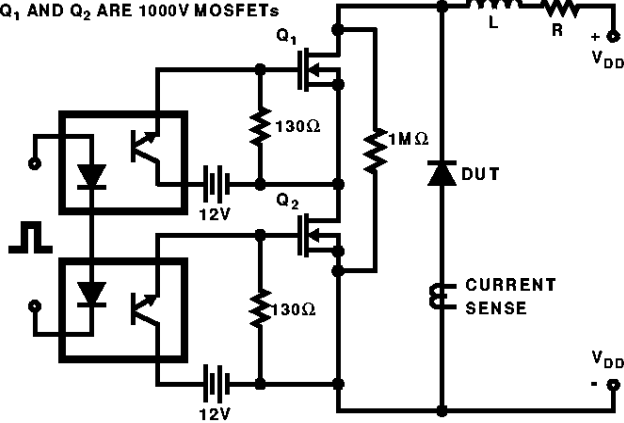


FIGURE 9. AVALANCHE ENERGY TEST CIRCUIT

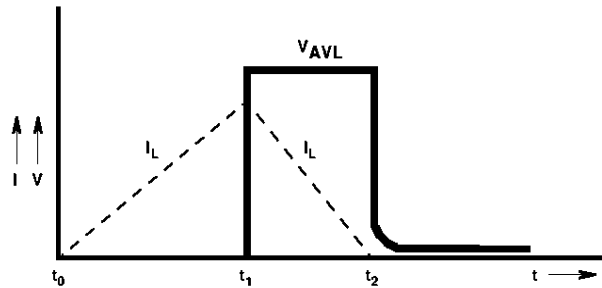


FIGURE 10. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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